

MSC40SM120JCU3
Datasheet
Buck Chopper SiC MOSFET Power Module

January 2020



Contents

Revision History.....	1
1.1 Revision 1.0.....	1
Product Overview.....	2
2.1 Features.....	3
2.2 Benefits.....	3
2.3 Applications.....	3
Electrical Specifications.....	4
3.1 SiC MOSFET Characteristics.....	4
3.2 SiC Chopper Diode Ratings and Characteristics.....	6
3.3 Thermal and Package Characteristics.....	6
3.4 Typical SiC MOSFET Performance Curves.....	7
3.5 Typical SiC Diode Performance Curves.....	10
Package Outline.....	11
4.1 Package Outline Drawing.....	11

1 Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

1.1 Revision 1.0

Revision 1.0 was published in January 2020. It is the first publication of this document.

2 Product Overview

The MSC40SM120JCU3 device is a 1200 V, 55 A full Silicon Carbide power module.

Figure 1 • Electrical Schematic of MSC70SM120JCU3 Device

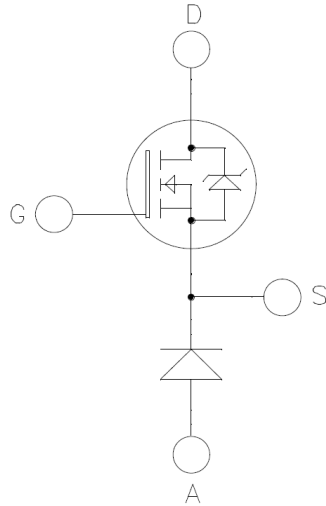
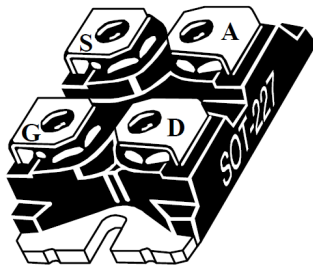


Figure 2 • SOT-227 Pinout Location



All ratings at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.

2.1 Features

The following are the features of MSC40SM120JCU3 device:

- SiC power MOSFET
 - Low $R_{DS(on)}$
 - High temperature performance
- SiC Schottky diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature independent switching behavior
 - Positive temperature coefficient on VF

2.2 Benefits

The following are the benefits of MSC40SM120JCU3 device:

- High efficiency converter
- Very low stray inductance
- Outstanding performance at high frequency operation
- Stable temperature behavior
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- RoHS compliant

2.3 Applications

The following are the applications of MSC40SM120JCU3 device:

- AC and DC motor control
- Switched mode power supplies

3 Electrical Specifications

This section provides the electrical specifications for the MSC40SM120JCU3 device.

3.1 SiC MOSFET Characteristics

The following table shows the absolute maximum ratings of MSC40SM120JCU3 device.

Table 1 • Absolute Maximum Ratings

Symbol	Parameters		Maximum Ratings	Unit
V_{DSS}	Drain–source voltage		1200	V
I_D	Continuous drain current	$T_C = 25^\circ\text{C}$	55	A
		$T_C = 80^\circ\text{C}$	44	
I_{DM}	Pulsed drain current		110	
V_{GS}	Gate–source voltage		–10/25	V
$R_{DS(on)}$	Drain–source ON resistance		50	m Ω
P_D	Power dissipation	$T_C = 25^\circ\text{C}$	245	W

The following table shows the electrical characteristics of MSC40SM120JCU3 device.

Table 2 • Electrical Characteristics

Symbol	Characteristics	Test Conditions		Min	Typ	Max	Unit
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$; $V_{DS} = 1200\text{ V}$			10	100	μA
$R_{DS(on)}$	Drain–source on resistance	$V_{GS} = 20\text{ V}$ $I_D = 40\text{ A}$	$T_C = 25^\circ\text{C}$		40	50	m Ω
			$T_C = 175^\circ\text{C}$		64		
$V_{GS(th)}$	Gate threshold voltage	$V_{GS} = V_{DS}$, $I_D = 1\text{ mA}$		1.8	2.7		V
I_{GSS}	Gate–source leakage current	$V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$				150	nA

The following table shows the dynamic characteristics of MSC40SM120JCU3 device.

Table 3 • Dynamic Characteristics

Symbol	Characteristics	Test Conditions		Min	Typ	Max	Unit
C _{iss}	Input capacitance	V _{GS} = 0 V V _{DS} = 1000 V f = 1 MHz			1990		pF
C _{oss}	Output capacitance				156		
C _{rss}	Reverse transfer capacitance				17		
Q _g	Total gate charge	V _{GS} = −5/20 V V _{Bus} = 800 V I _D = 40 A			137		nC
Q _{gs}	Gate–source charge				29		
Q _{gd}	Gate–drain charge				31		
T _{d(on)}	Turn-on delay time	V _{GS} = −5/20 V V _{Bus} = 600 V I _D = 40 A R _{Gon} = 10 Ω R _{Goff} = 5.8 Ω			30		ns
T _r	Rise time				30		
T _{d(off)}	Turn-off delay time				50		
T _f	Fall time				25		
E _{on}	Turn on energy	Inductive Switching V _{GS} = −5/20 V V _{Bus} = 600 V I _D = 40A R _{Gon} = 10 Ω R _{Goff} = 5.8 Ω	T _J = 150°C		0.79		mJ
E _{off}	Turn off energy		T _J = 150°C		0.53		mJ
R _{Gint}	Internal gate resistance				1.2		Ω
R _{thJC}	Junction-to-case thermal resistance					0.61	°C/W

The following table shows the body diode ratings and characteristics of MSC40SM120JCU3 device.

Table 4 • Body Diode Ratings and Characteristics

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Unit
V_{SD}	Diode forward voltage	$V_{GS} = 0\text{ V}$; $I_{SD} = 40\text{ A}$		5.4		V
t_{rr}	Reverse recovery time	$I_{SD} = 40\text{ A}$; $V_{GS} = -5\text{ V}$ $V_R = 800\text{ V}$; $di_f/dt = 1800\text{ A}/\mu\text{s}$		31		ns
Q_{rr}	Reverse recovery charge			610		nC
I_{rr}	Reverse recovery current			40		A

3.2 SiC Chopper Diode Ratings and Characteristics

The following table shows the SiC chopper diode ratings and characteristics of MSC40SM120JCU3 device.

Table 5 • SiC Chopper Diode Ratings and Characteristics

Symbol	Characteristics	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Peak repetitive reverse voltage					1200	V
I_{RM}	Reverse leakage current	$V_R = 1200\text{ V}$	$T_j = 25\text{ }^{\circ}\text{C}$		10	200	μA
			$T_j = 175\text{ }^{\circ}\text{C}$		150		
I_F	DC forward current		$T_C = 100\text{ }^{\circ}\text{C}$		30		A
V_F	Diode forward voltage	$I_F = 30\text{ A}$	$T_j = 25\text{ }^{\circ}\text{C}$		1.5	1.8	V
			$T_j = 175\text{ }^{\circ}\text{C}$		2.1		
Q_C	Total capacitive charge	$V_R = 600\text{ V}$			130		nC
C	Total capacitance	$f = 1\text{ MHz}, V_R = 400\text{ V}$			141		pF
		$f = 1\text{ MHz}, V_R = 800\text{ V}$			105		
R_{thJC}	Junction-to-case thermal resistance					0.9	$^{\circ}\text{C/W}$

3.3 Thermal and Package Characteristics

The following table shows the thermal and package characteristics of MSC40SM120JCU3 device.

Table 6 • Thermal and Package Characteristics

Symbol	Characteristics	Min	Typ	Max	Unit
V_{ISOL}	RMS isolation voltage, any terminal to case $t = 1\text{ min}$, 50/60 Hz	2500			V
T_{STG}	Storage temperature range	-55		175	$^{\circ}\text{C}$
T_J	Operating junction temperature range	-55		175	
T_{JOP}	Recommended junction temperature under switching conditions	-55		$T_{Jmax} - 25$	
Torque	Terminals and mounting screws			1.1	N.m
Wt	Package weight		29.2		g

3.4 Typical SiC MOSFET Performance Curves

The following images show the SiC MOSFET performance curves of the MSC40SM120JCU3 device.

Figure 3 • Maximum Thermal Impedance

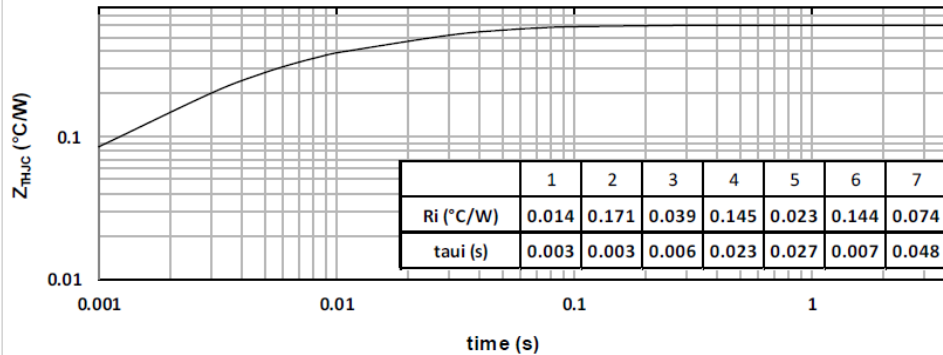


Figure 4 • Output Characteristics, $T_J = 25^\circ\text{C}$

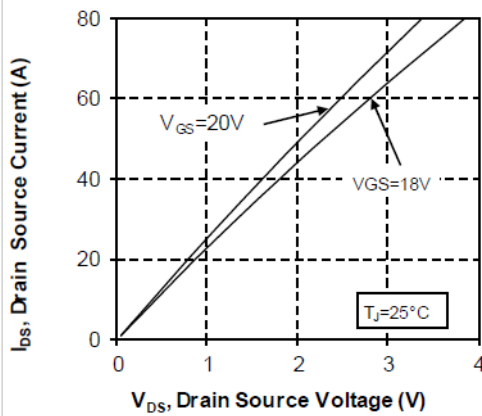


Figure 5 • Output Characteristics, $T_J = 175^\circ\text{C}$

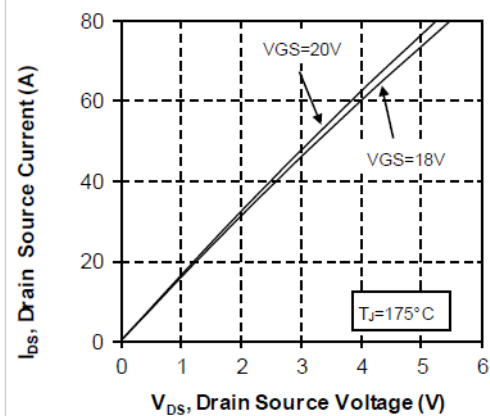


Figure 6 • Normalized $R_{DS(on)}$ vs. Temperature

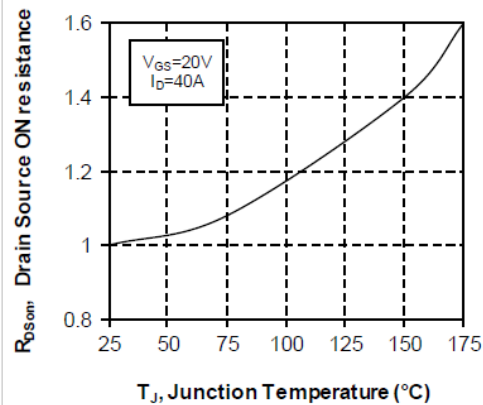


Figure 7 • Transfer Characteristics

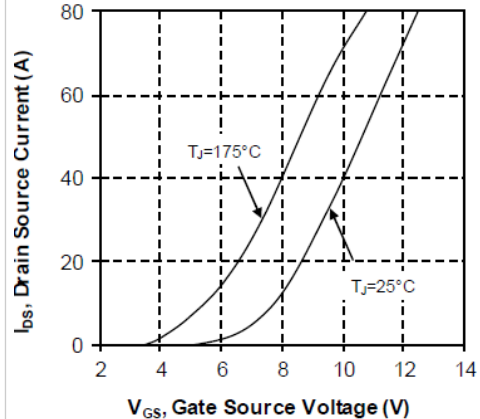


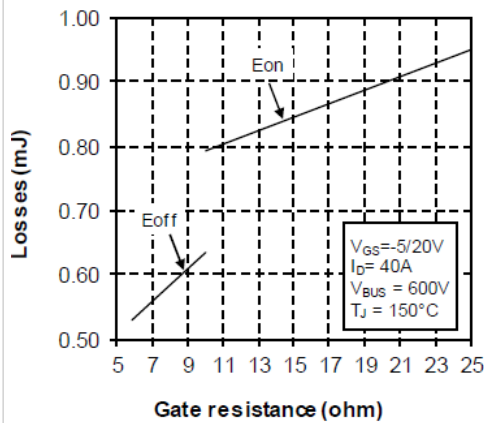
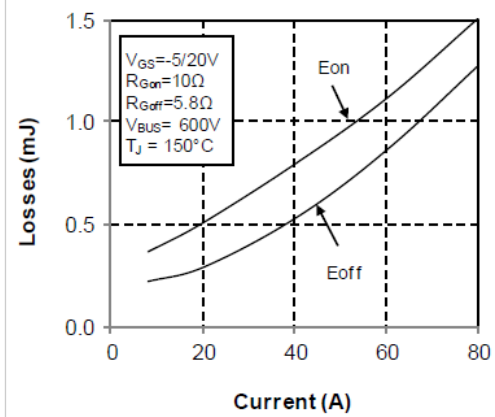
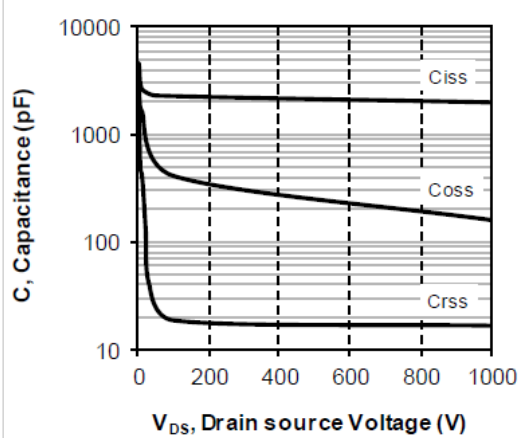
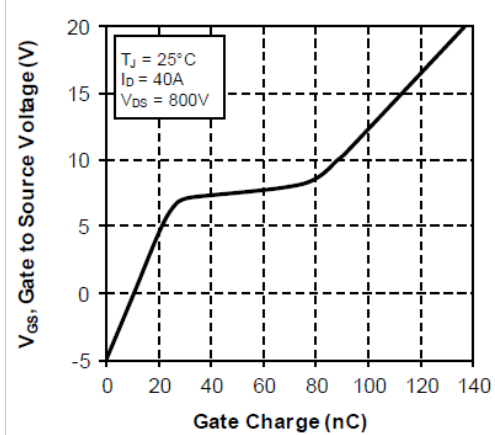
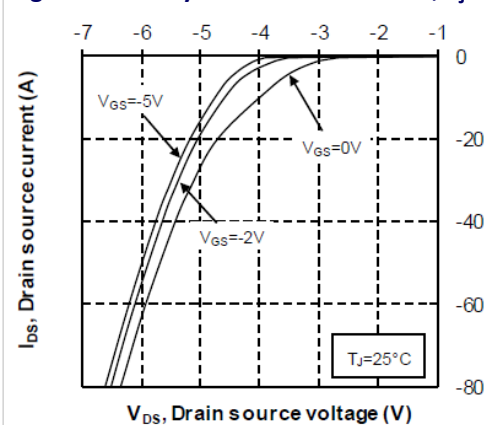
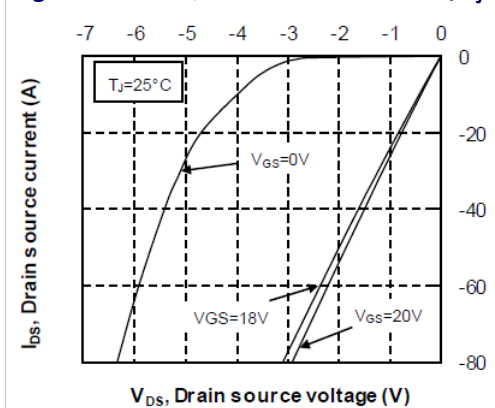
Figure 8 • Switching Energy vs. R_g **Figure 9 • Switching Energy vs. Current****Figure 10 • Capacitance vs. Drain Source Voltage****Figure 11 • Gate Charge vs. Gate Source Voltage****Figure 12 • Body Diode Characteristics, $T_J = 25^\circ C$** **Figure 13 • 3rd Quadrant Characteristics, $T_J = 25^\circ C$** 

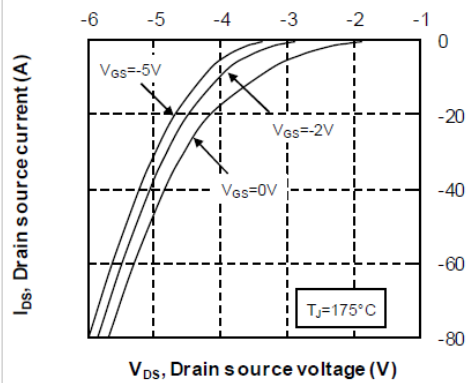
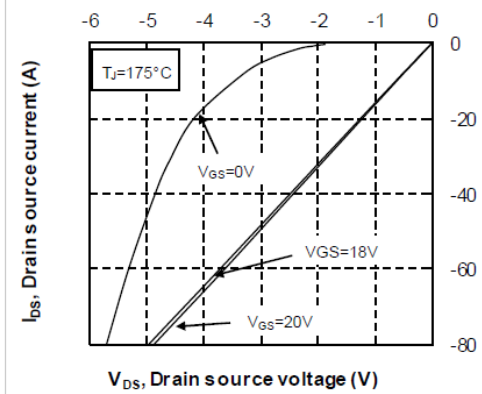
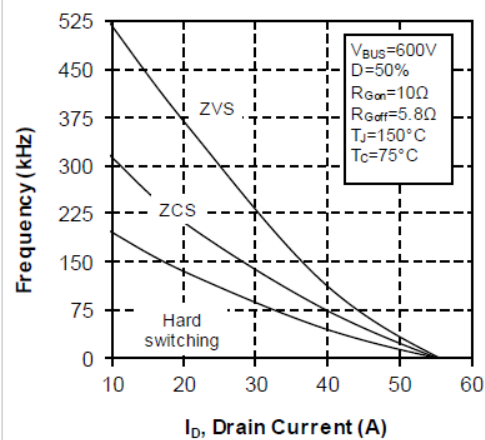
Figure 14 • Body Diode Characteristics, $T_J=175^\circ\text{C}$ Figure 15 • 3rd Quadrant Characteristics, $T_J=175^\circ\text{C}$ 

Figure 16 • Operating Frequency vs. Drain Current



3.5 Typical SiC Diode Performance Curves

The following images show the SiC diode performance curves of MSC40SM120JCU3 device.

Figure 17 • Maximum Thermal Impedance

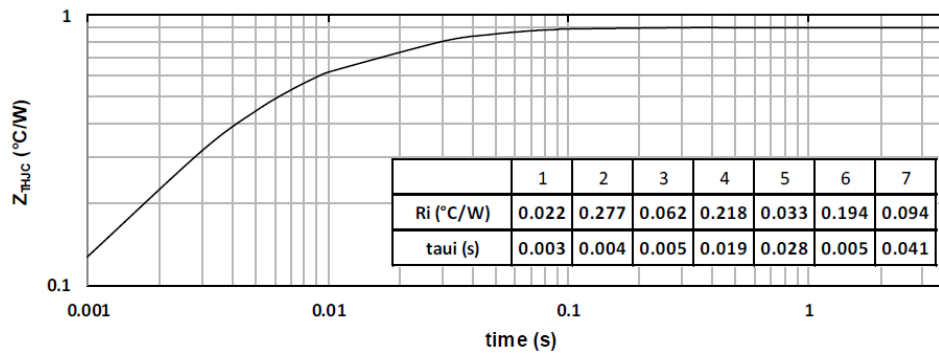


Figure 18 • Forward Characteristics

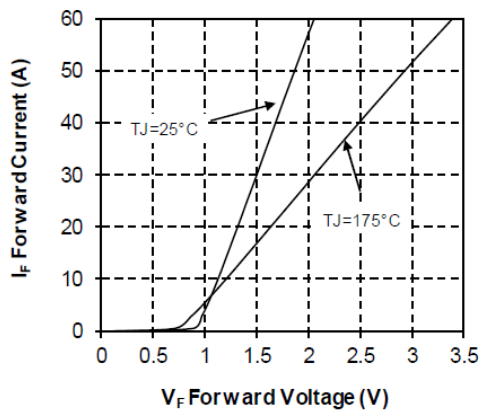
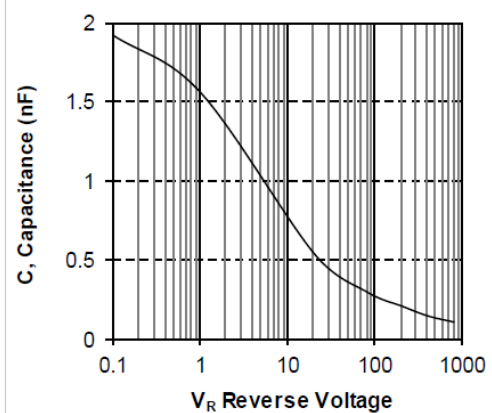


Figure 19 • Capacitance vs. Reverse Voltage



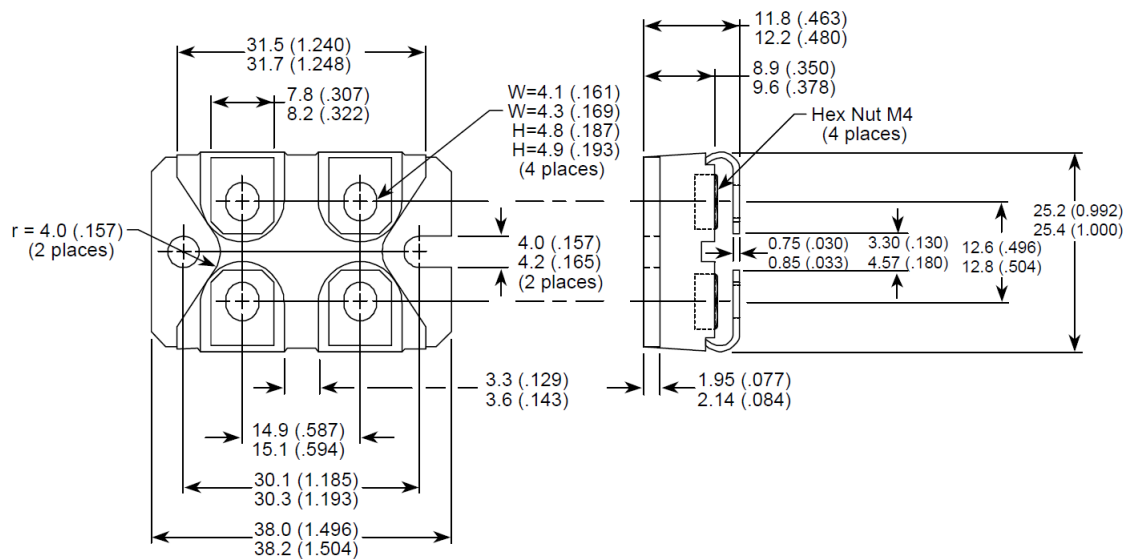
4 Package Specification

The following section shows the package specification of MSC40SM120JCU3 device.

4.1 Package Outline Drawing

The following image illustrates the package outline drawing of MSC40SM120JCU3 device. The dimensions are in millimeters and (inches).

Figure 20 • Package Outline Drawing



**Microsemi**

2355 W. Chandler Blvd.
 Chandler, AZ 85224 USA

Within the USA: +1 (480) 792-7200
 Fax: +1 (480) 792-7277

www.microsemi.com © 2020 Microsemi and its corporate affiliates. All rights reserved. Microsemi and the Microsemi logo are trademarks of Microsemi Corporation and its corporate affiliates. All other trademarks and service marks are the property of their respective owners.

Microsemi's product warranty is set forth in Microsemi's Sales Order Terms and Conditions. Information contained in this publication is provided for the sole purpose of designing with and using Microsemi products. Information regarding device applications and the like is provided only for your convenience and may be superseded by updates. Buyer shall not rely on any data and performance specifications or parameters provided by Microsemi. It is your responsibility to ensure that your application meets with your specifications. THIS INFORMATION IS PROVIDED "AS IS." MICROSEMI MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, NON-INFRINGEMENT, MERCHANTABILITY OR FITNESS FOR A PARTICULAR PURPOSE. IN NO EVENT WILL MICROSEMI BE LIABLE FOR ANY INDIRECT, SPECIAL, PUNITIVE, INCIDENTAL OR CONSEQUENTIAL LOSS, DAMAGE, COST OR EXPENSE WHATSOEVER RELATED TO THIS INFORMATION OR ITS USE, HOWEVER CAUSED, EVEN IF MICROSEMI HAS BEEN ADVISED OF THE POSSIBILITY OR THE DAMAGES ARE FORESEEABLE. TO THE FULLEST EXTENT ALLOWED BY LAW, MICROSEMI'S TOTAL LIABILITY ON ALL CLAIMS IN RELATED TO THIS INFORMATION OR ITS USE WILL NOT EXCEED THE AMOUNT OF FEES, IF ANY, YOU PAID DIRECTLY TO MICROSEMI FOR THIS INFORMATION. Use of Microsemi devices in life support, mission-critical equipment or applications, and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend and indemnify Microsemi from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microsemi intellectual property rights unless otherwise stated.

Microsemi Corporation, a subsidiary of Microchip Technology Inc. (Nasdaq: MCHP), and its corporate affiliates are leading providers of smart, connected and secure embedded control solutions. Their easy-to-use development tools and comprehensive product portfolio enable customers to create optimal designs which reduce risk while lowering total system cost and time to market. These solutions serve more than 120,000 customers across the industrial, automotive, consumer, aerospace and defense, communications and computing markets. Headquartered in Chandler, Arizona, the company offers outstanding technical support along with dependable delivery and quality. Learn more at **www.microsemi.com**.

MSCC-0344-DS-01063-1.0-0120